

AMENDMENTS

In The Claims

Claim 1. (currently amended) An alignment mark configuration, which is applicable on a substrate, the alignment mark configuration comprising:

an alignment mark on the substrate, wherein the alignment mark comprises a plurality of recesses and a spacing between the neighboring recesses is "d", wherein the recess has a width of about 2 microns to about 6 microns and the spacing "d" is a range of about 6 microns to about 12 microns; and

a trench not belonging to the alignment mark, wherein a spacing between the trench and the alignment mark is of a range between about 5d to about 80d.

Claim 2. (Original) The alignment mark configuration according to claim 1, wherein the recesses include a plurality of trenches formed by a shallow trench isolation fabrication process.

Claim 3. (Original) The alignment mark configuration according to claim 1, wherein the trench includes a shallow trench isolation structure.

Claim 4. (previously presented) The alignment mark configuration according to claim 1, wherein each of the recesses is rectangular-like.

Claim 5. (previously presented) The alignment mark configuration according to claim 1, wherein each of the recesses is rectangular-like and is arranged in one direction side by side at

long sides of the rectangular-like recesses.

Claim 6. (currently amended) An alignment mark configuration, which is applicable on a substrate, the alignment mark configuration comprising:

an alignment mark on the substrate, wherein the alignment mark comprises a plurality of recesses, wherein each of the recesses is rectangular-like and a spacing between the neighboring recesses is "d"; and

a trench not belonging to the alignment mark, wherein a spacing between the trench and the alignment mark is of a range between about 5d to about 80d.